Semiconductor device and manufacturing method thereof

Patent number: EP1045443
Publication date: 2000-10-18
Inventor: DOTTA YOSHIHISA (JP); SAZA YASUYUKI (JP); TAMAKI KAZUO (JP)
Applicant: SHARP KK (JP)
Classification:
- international: ***H01L21/56; H01L21/98; H01L23/31; H01L25/065;*** **H01L21/02; H01L21/70; H01L23/28; H01L25/065;** (IPC1-7): H01L25/065; H01L21/98
- european: H01L21/56F; H01L21/98; H01L23/31H2; H01L25/065S
Application number: EP20000301638 20000301
Priority number(s): JP19990107106 19990414

Also published as:
US6353263 (B1)
JP2000299431 (A
EP1045443 (A3)
CN1161834C (C)

Cited documents:
WO9912208
EP0915505
US2002004258
JP63084128

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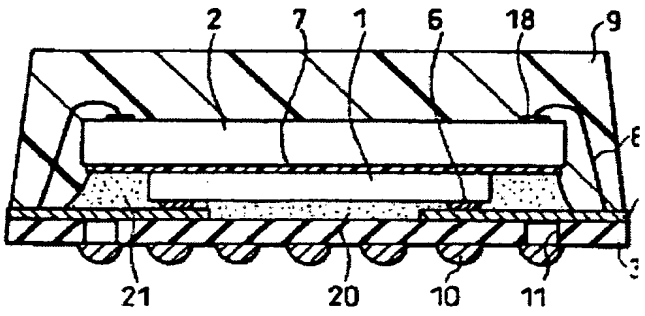
Abstract of **EP1045443**

When a first semiconductor chip is installed on a circuit substrate by using an anisotropic conductive bonding agent, one portion thereof is allowed to protrude outside the first semiconductor chip. A second semiconductor chip is installed on the first semiconductor chip and a support portion formed by the protruding resin. The protruding portion of the second semiconductor chip is supported by the support portion from under. Thus, in a semiconductor device having a plurality of laminated semiconductor chips in an attempt to achieve a high density, even when, from a semiconductor chip stacked on a circuit substrate, one portion of a semiconductor chip stacked thereon protrudes, it is possible to carry out a better wire bonding process on electrodes formed on the protruding portion.

FIG. 1



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